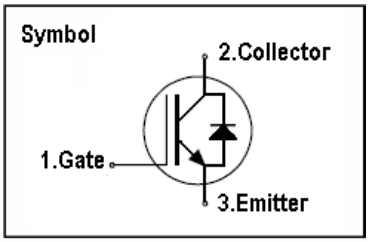
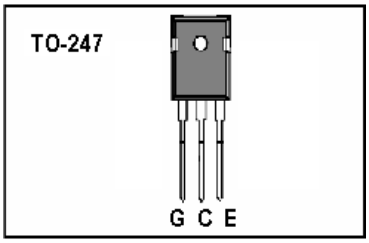
LGEGW40N120F

1200V/40A Trench Field Stop IGBT

Features

- 1200V,40A
- $V_{CE(sat)(typ.)}$=2.1V@V_{GE}=15V,I_C=40A
- High speed switching
- Higher system efficiency
- Soft current turn-off waveforms





General Description

LGE Trench FS IGBTs offer lower losses and higher energy efficiency for application such as IH (induction heating),UPS, general inverter and other soft switching applications.

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 30	V
I_C	Continuous Collector Current (T_C=25℃)	80	A
	Continuous Collector Current (T_C=100℃)	40	A
I_{CM}	Pulsed Collector Current (Note 1)	120	A
I_F	Diode Continuous Forward Current (T_C=100℃)	40	A
I_{FM}	Diode Maximum Forward Current (Note 1)	120	A
t_{sc}	Short Circuit Withstand Time	10	us
P_D	Maximum Power Dissipation (T_C=25℃)	300	W
	Maximum Power Dissipation (T_C=100℃)	110	W
T_J	Operating Junction Temperature Range	-55 to +150	℃
T_{STG}	Storage Temperature Range	-55 to +150	℃

Thermal Characteristics

Symbol	Parameter	Max.	Units
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to case for IGBT	0.42	℃/ W
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to case for Diode	0.8	℃/ W
$R_{th\ j\text{-}a}$	Thermal Resistance, Junction to Ambient	40	℃/ W

Electrical Characteristics (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{CES}	Collector-Emitter Breakdown Voltage	V_{GE}= 0V, I_C= 1mA	1200	-	-	V
I_{CES}	Collector-Emitter Leakage Current	V_{CE}= 1200V, V_{GE}= 0V	-	-	100	uA
I_{GES}	Gate Leakage Current, Forward	V_{GE}=30V, V_{CE}= 0V	-	-	100	nA
	Gate Leakage Current, Reverse	V_{GE}= -30V, V_{CE}= 0V	-	-	100	nA
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE}= V_{CE}, I_C= 250uA	4.5	-	6.5	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	V_{GE}=15V, I_C= 40A	-	2.1	2.6	V
Q_g	Total Gate Charge	V_{CC}=600V V_{GE}=15V I_C=40A	-	107		nC
Q_{ge}	Gate-Emitter Charge		-	36		nC
Q_{gc}	Gate-Collector Charge		-	58		nC
$t_{d(on)}$	Turn-on Delay Time	V_{CC}=600V V_{GE}=15V I_C=40A R_G=10Ω Inductive Load T_C=25 ℃	-	62	-	ns
t_r	Turn-on Rise Time		-	72	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	460	-	ns
t_f	Turn-off Fall Time		-	43	-	ns
Eon	Turn-on Switching Loss		-	3.2	-	mJ
Eoff	Turn-off Switching Loss		-	2.0	-	mJ
Ets	Total Switching Loss		-	5.2	-	mJ
C_{ies}	Input Capacitance	V_{CE}=30V V_{GE}=0V f = 1MHz	-	3000	-	pF
C_{oes}	Output Capacitance		-	75	-	pF
C_{res}	Reverse Transfer Capacitance		-	28	-	pF

Electrical Characteristics of Diode (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_F	Diode Forward Voltage	I_F=40A	-	2.2	3.2	V
t_{rr}	Diode Reverse Recovery Time	V_{CE} = 600V I_F= 40A dI_F/dt = 200A/us	-	250		ns
I_{rr}	Diode peak Reverse Recovery Current		-	10		A
Q_{rr}	Diode Reverse Recovery Charge		-	1350		nC

Notes：

1. Repetitive Rating: Pulse width limited by maximum junction temperature

Typical Performance Characteristics

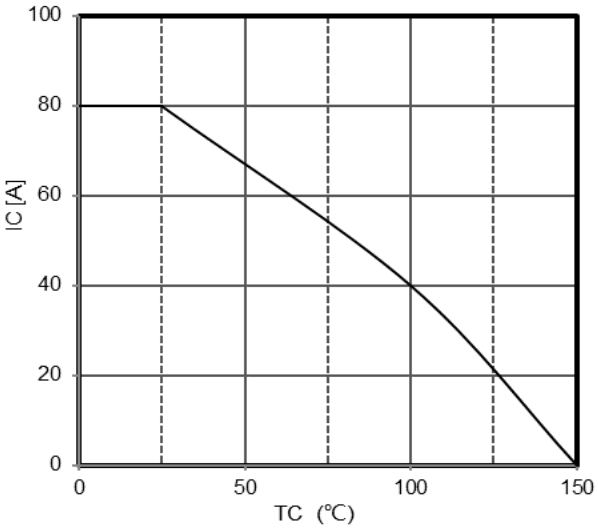


Figure1:maximum DC collector current VS. case temprature

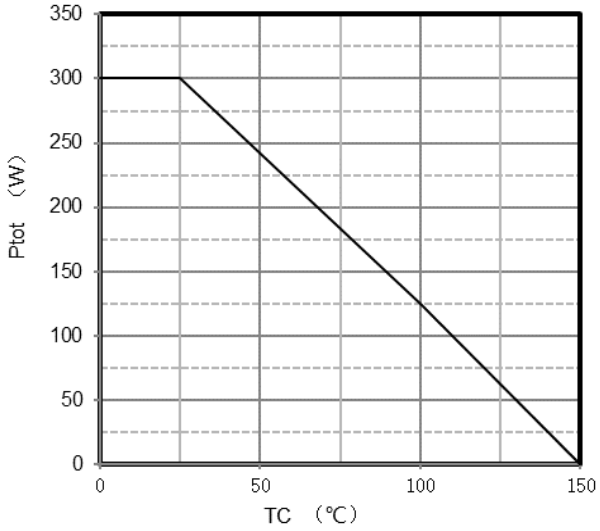


Figure2:power dissipation VS. case temprature

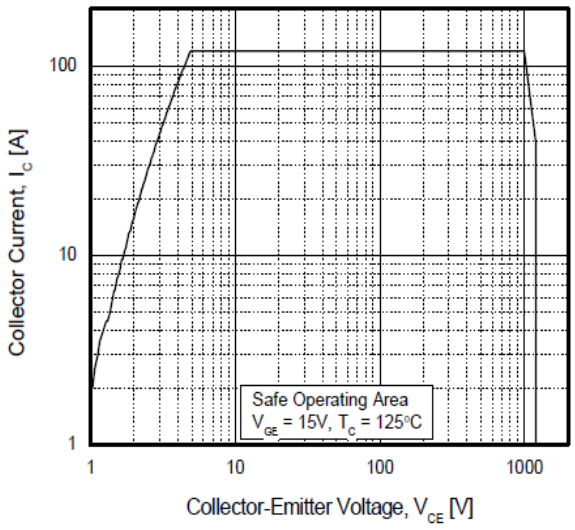


Figure3:reverse bias SOA,TJ=125℃,VGE=15V

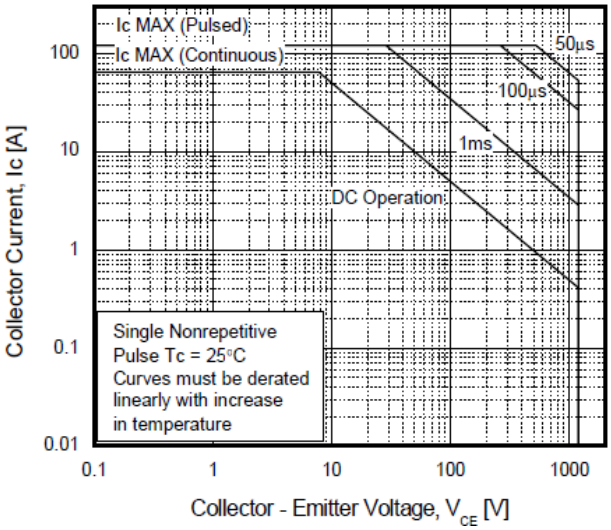


Figure4:forward SOA,TC=25℃,TJ≤150℃

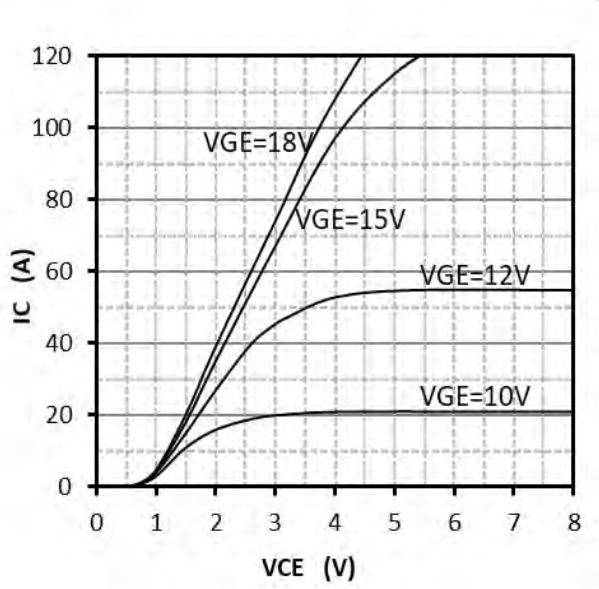


Figure5:typical IGBT output characteristics,

TJ=25℃;tp=300us

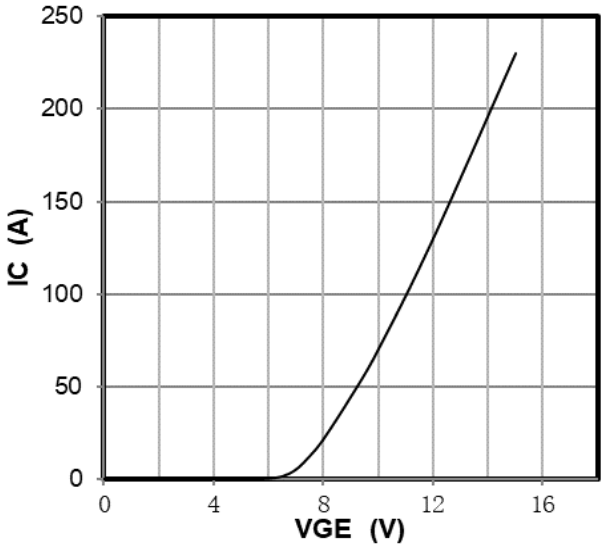


Figure6:typical trans characteristics,

VCE=20V,tp=20us

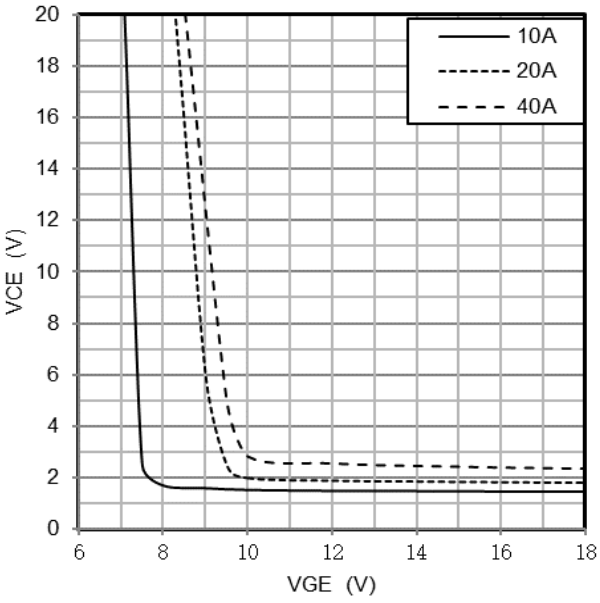


Figure7: typical VCE VS. VGE,TJ=25℃

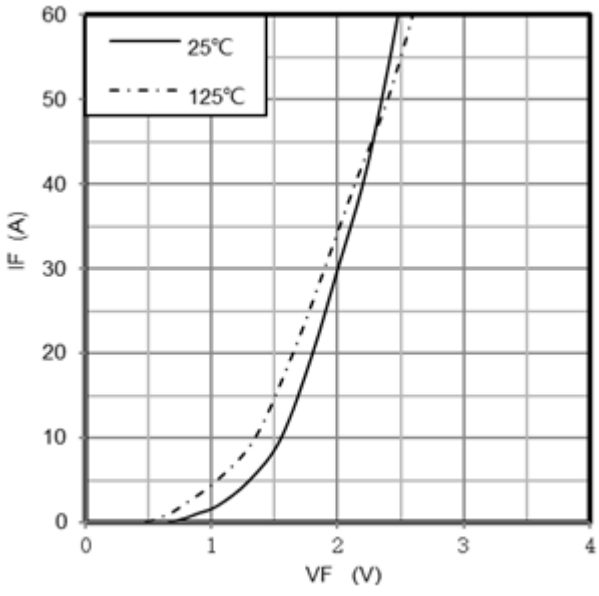


Figure8:typical diode forward characteristic,tp=300us

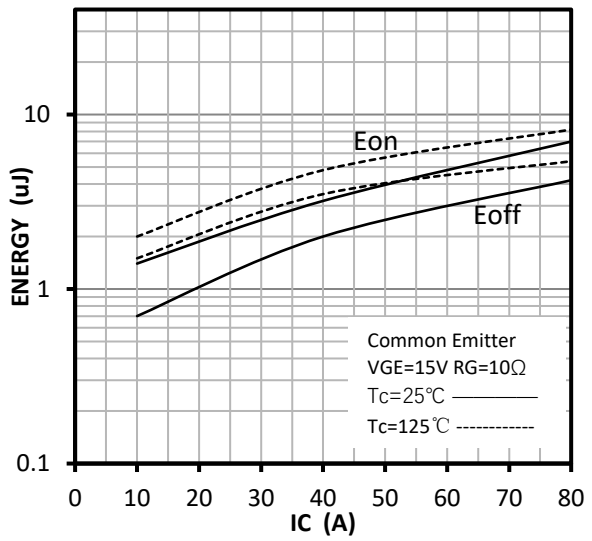


Figure9: typical energy loss VS. IC, TC=25℃,

L=500uH， VCE=600V,VGE=15V,Rg=10Ω

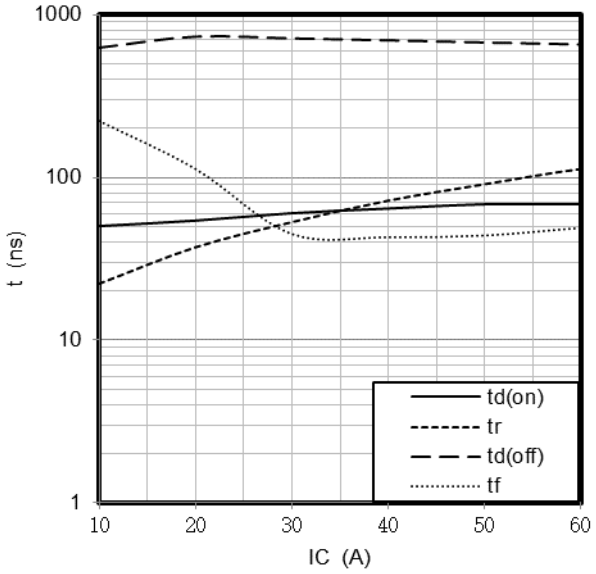


Figure10: typical switching time VS. IC, TC=25℃,

L=500uH, VCE=600V,VGE=15V,Rg=28Ω

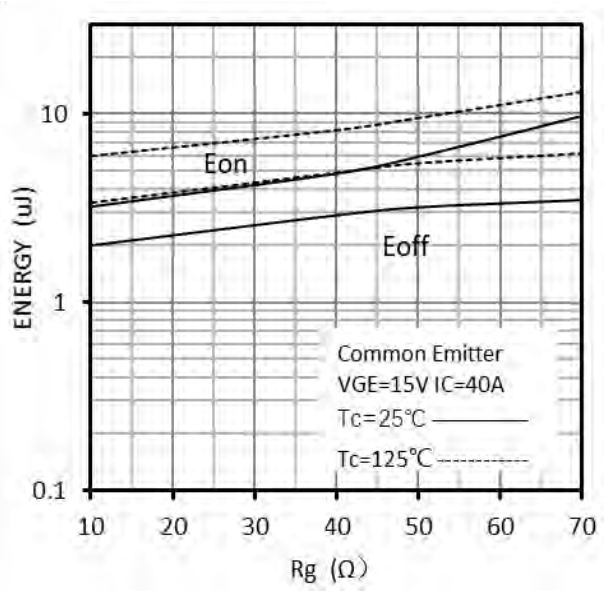


Figure11: typical energy loss VS. Rg,TC=25℃,

L=500uH, VCE=600V, VGE=15V ,IC=40A

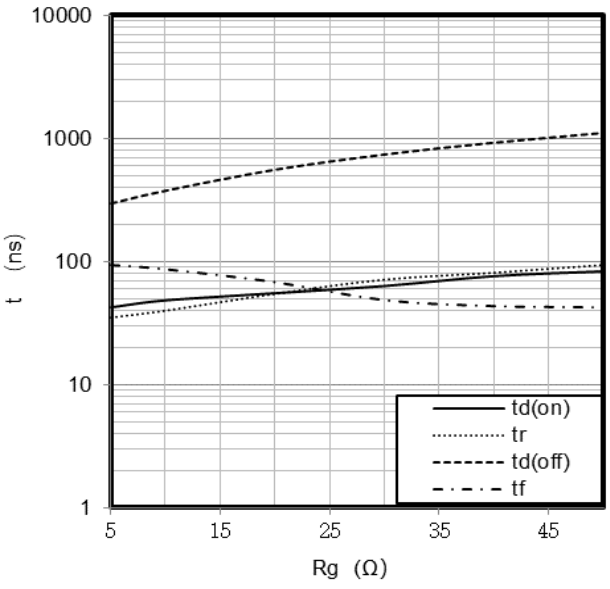


Figure12: typical switching time VS. Rg,TC=25℃,

L=500uH,VCE=600V,VGE=15V,IC=40A

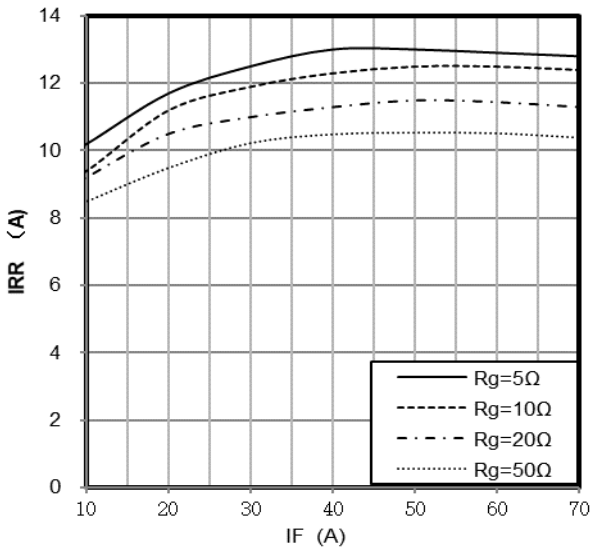


Figure13: typical diode IRR VS. IF, TC=25℃

VCC=600V, VGE=15V

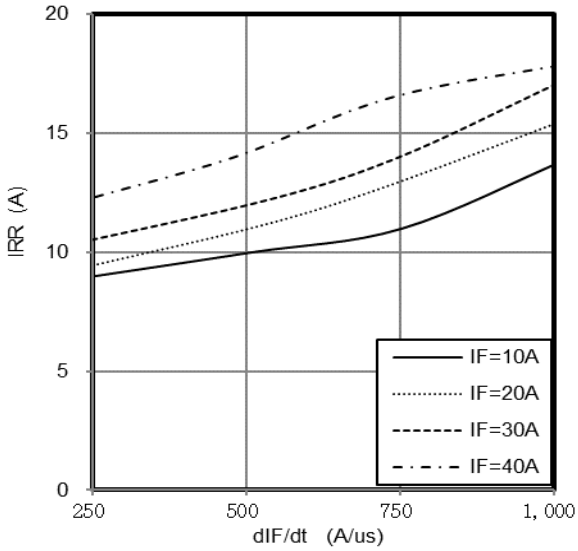


Figure14:typical diode IRR VS. dIF/dt

VCC=600V,VGE=15V

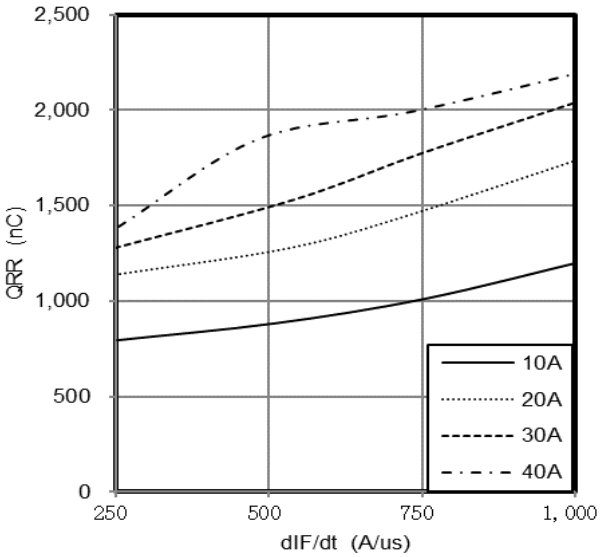


Figure15: typical diode QRR VS. dIF/dt

VCC=600V , VGE=15V

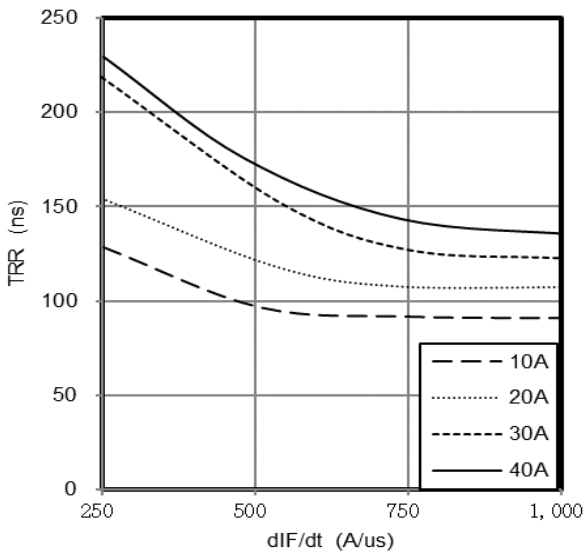


Figure16: typical diode TRR VS. dIF/dt,

VCC=600V,VGE=15V

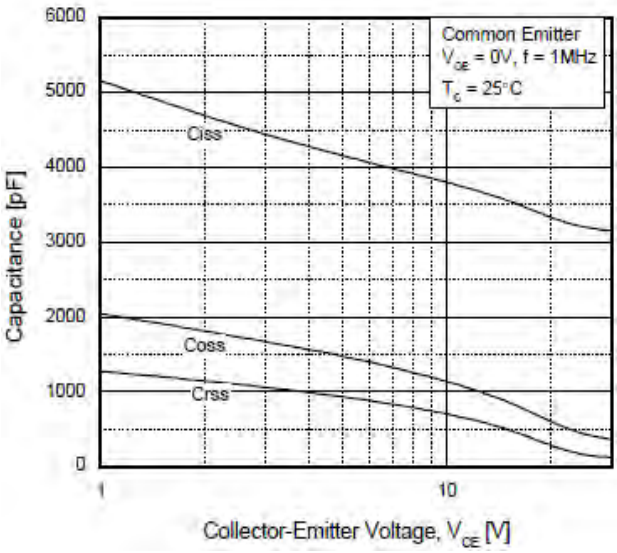


Figure17:typical capacitance VS. VCE, VGE=0V,f=100kHz

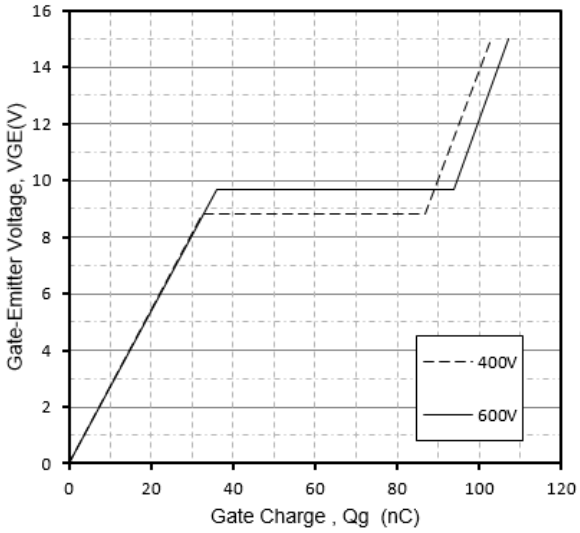


Figure18:typical gate charge VS. VGE,IC=40A

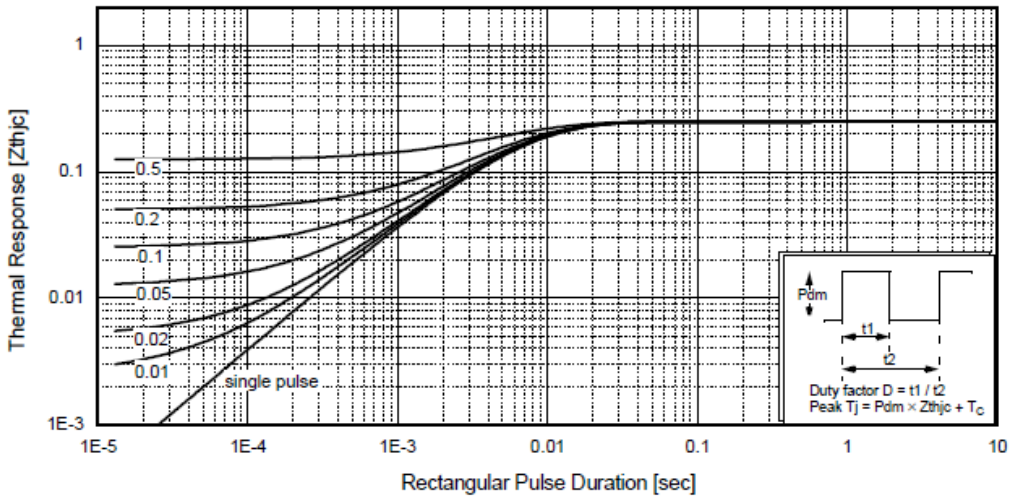
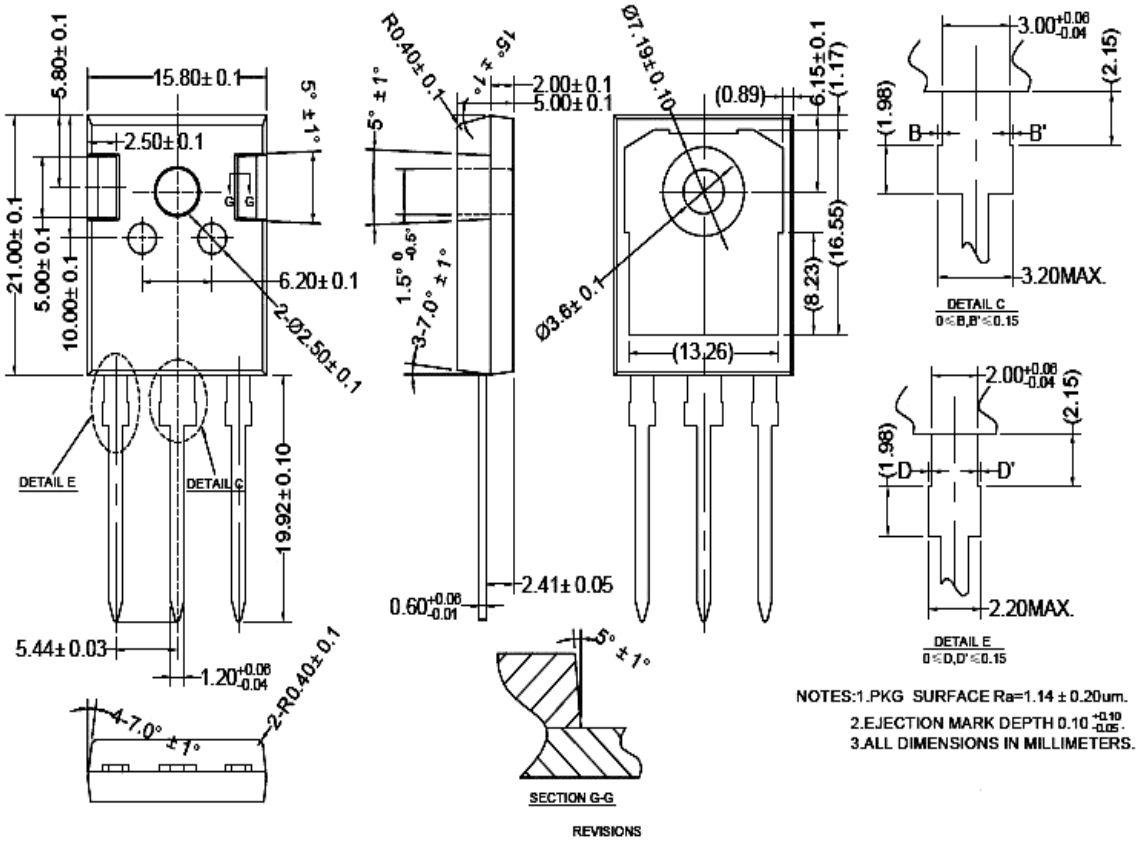


Figure19: normalized transient thermal impedance, junction-to-case

Note1.Duty factor D=t1/t2 Note2: peak TJ=PDM × Zthjc + TC

TO247 PACKAGE OUTLINE



公差标注	公差值	表面粗糙度
0	±0.2	Ra3.2~6.3
0.0	±0.1	Ra1.6~3.2
0.00	±0.01	Ra0.8~1.6
0.000	±0.005	Ra0.4~0.8
0.0000	±0.002	Ra0.2~0.4

0≤D,D'≤0.15
NOTES:1.PKG SURFACE Ra=1.14 ± 0.20um.
2.EJECTION MARK DEPTH 0.10 +0.10 -0.05.
3.ALL DIMENSIONS IN MILLIMETERS.